

N-Channel Enhancement Mode Power MOSFET

DESCRIPTION

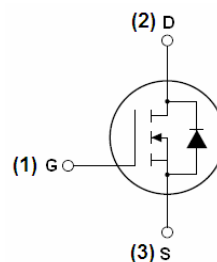
The HM4410B uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

GENERAL FEATURES

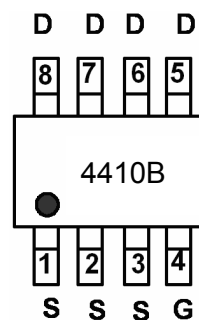
- $V_{DS} = 30V, I_D = 12A$
 $R_{DS(ON)} < 11m\Omega @ V_{GS}=10V$
 $R_{DS(ON)} < 13m\Omega @ V_{GS}=4.5V$
- High density cell design for ultra low R_{dson}
- Fully characterized Avalanche voltage and current

Application

- Power switching application
- Hard Switched and High Frequency Circuits
- Uninterruptible Power Supply



Schematic diagram



Marking and pin Assignment



SOP-8 top view

Package Marking And Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
4410B	HM4410B	SOP-8	Ø330mm	12mm	2500 units

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	±20	V
Drain Current-Continuous	I_D	12	A
Drain Current-Continuous($T_C=100^\circ C$)	$I_D (100^\circ C)$	7	A
Pulsed Drain Current	I_{DM}	60	A
Maximum Power Dissipation	P_D	3	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	°C

Thermal Characteristic

Thermal Resistance, Junction-to-Case(Note 2)	$R_{\theta JC}$	50	°C/W
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Electrical Characteristics (TA=25°C unless otherwise noted)

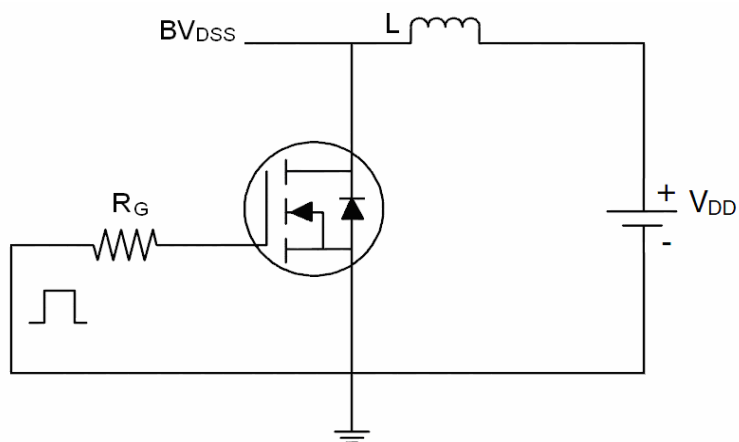
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	30	33	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =30V, V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1	1.8	3	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =12A	-	9	11	mΩ
		V _{GS} =4.5V, I _D =5A	-	11	13	
Forward Transconductance	g _{FS}	V _{DS} =5V, I _D =12A	15	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{ISS}	V _{DS} =15V, V _{GS} =0V, F=1.0MHz	-	1550	-	PF
Output Capacitance	C _{OSS}		-	300	-	PF
Reverse Transfer Capacitance	C _{rss}		-	180	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =25V, I _D =1A V _{GS} =10V, R _{GEN} =6Ω	-	30	-	nS
Turn-on Rise Time	t _r		-	20	-	nS
Turn-Off Delay Time	t _{d(off)}		-	100	-	nS
Turn-Off Fall Time	t _f		-	80	-	nS
Total Gate Charge	Q _g	V _{DS} =15V, I _D =12A, V _{GS} =5V	-	13	-	nC
Gate-Source Charge	Q _{gs}		-	5.5	-	nC
Gate-Drain Charge	Q _{gd}		-	3.5	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V, I _S =12A	-	-	1.2	V
Diode Forward Current (Note 2)	I _S		-	-	12	A

Notes:

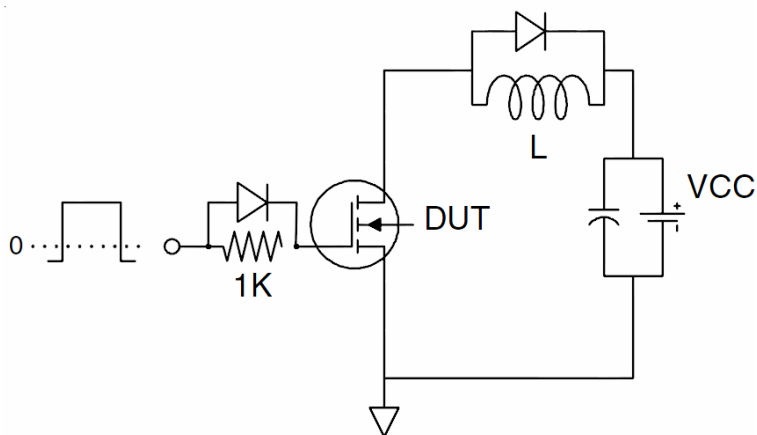
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production

Test circuit

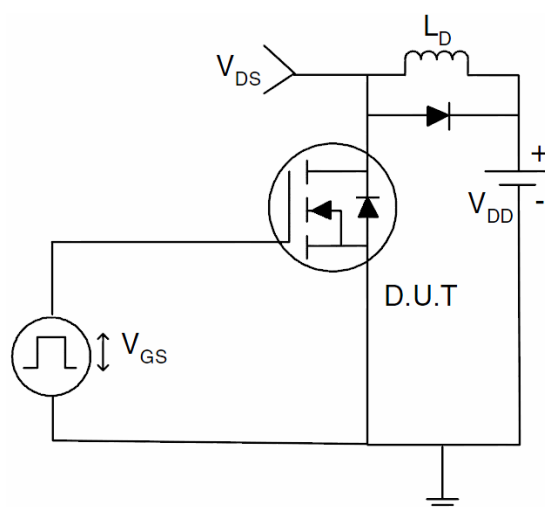
1) E_{AS} test Circuits



2) Gate charge test Circuit:



3) Switch Time Test Circuit:



TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS (Curves)

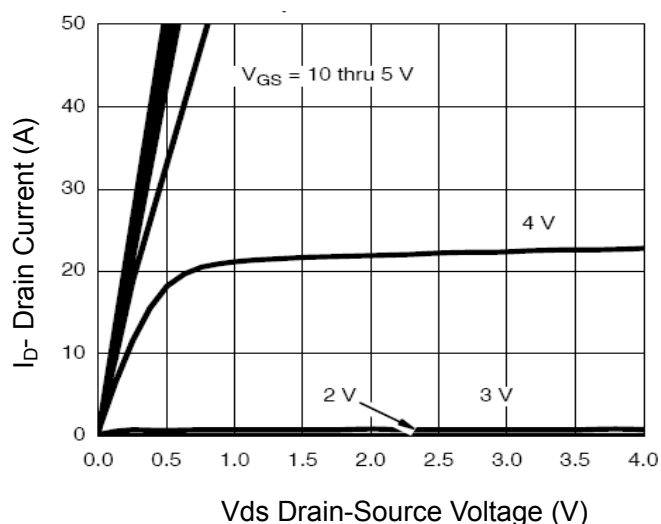


Figure 1 Output Characteristics

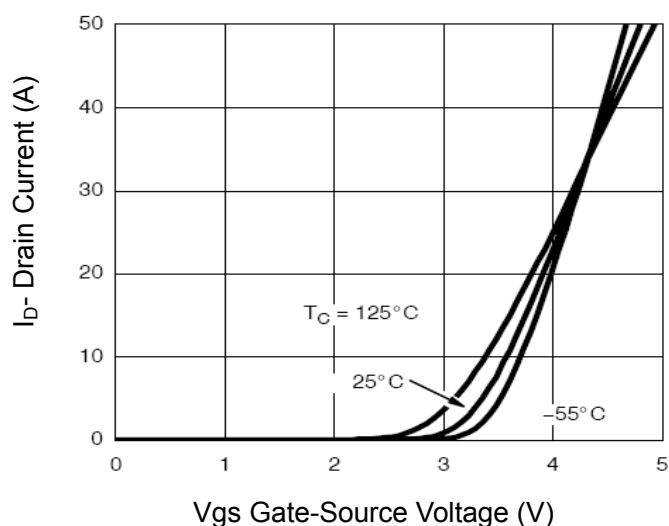


Figure 2 Transfer Characteristics

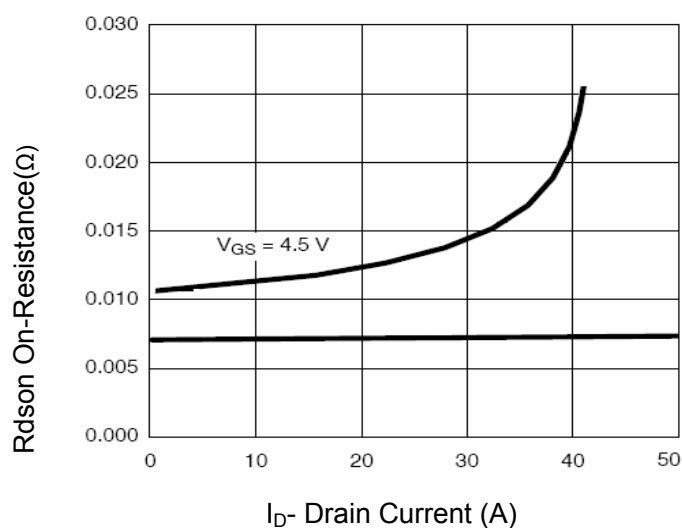


Figure 3 Rdson- Drain Current

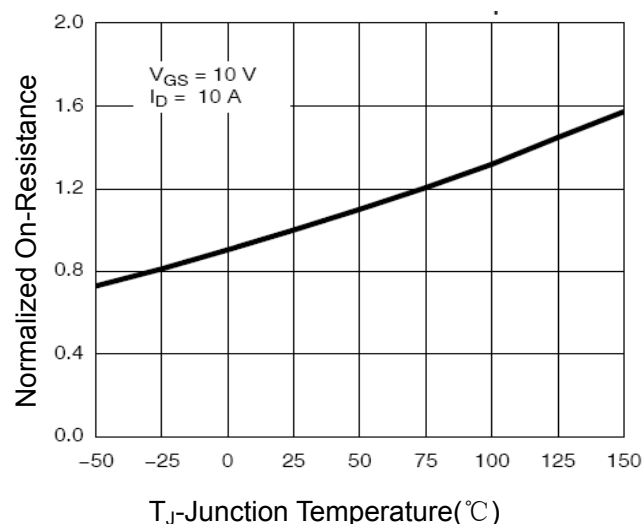


Figure 4 Rdson-Junction Temperature

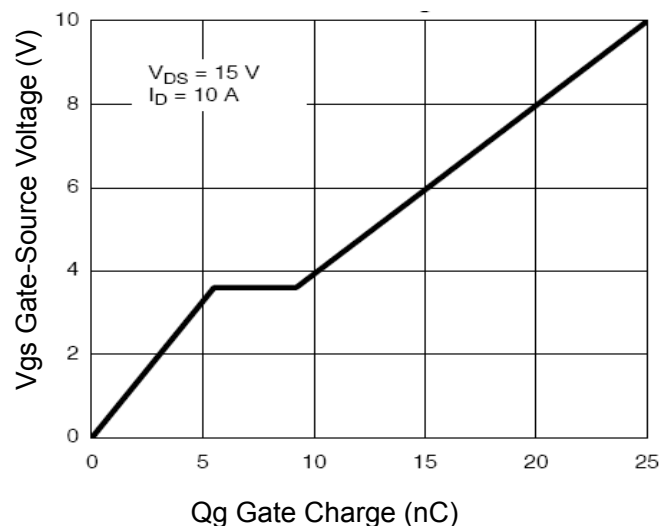


Figure 5 Gate Charge

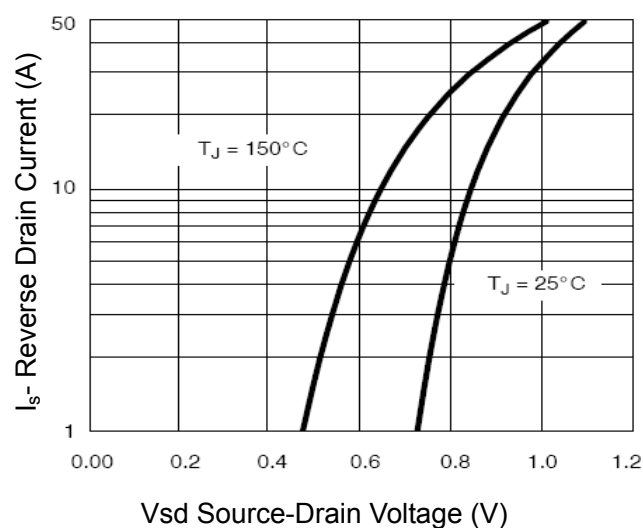


Figure 6 Source- Drain Diode Forward

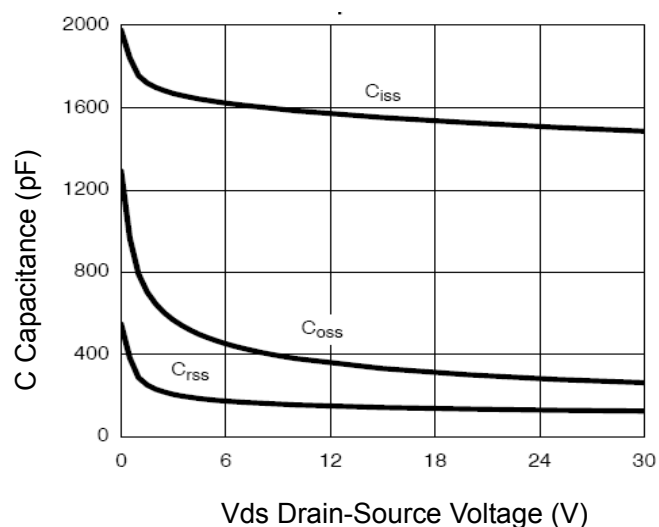


Figure 7 Capacitance vs Vds

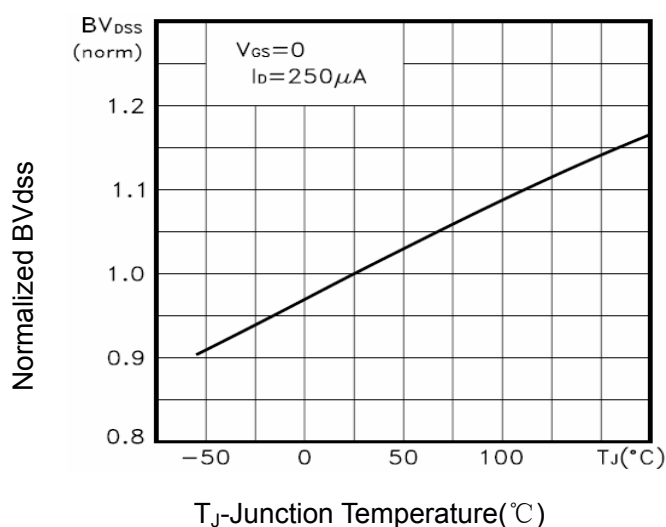


Figure 9 BV_{DSS} vs Junction Temperature

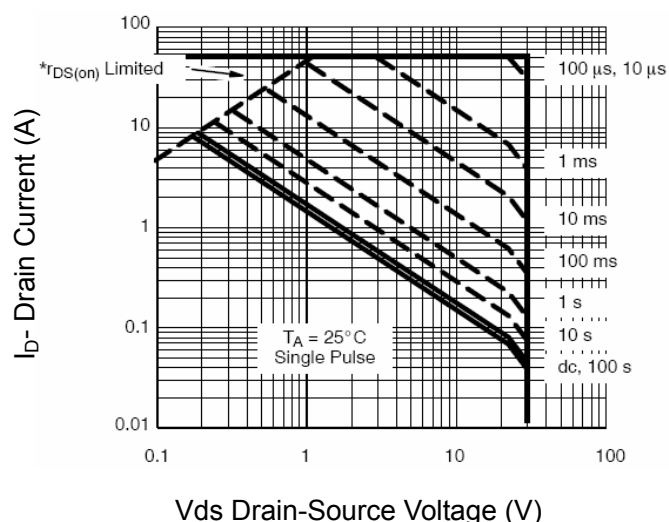


Figure 8 Safe Operation Area

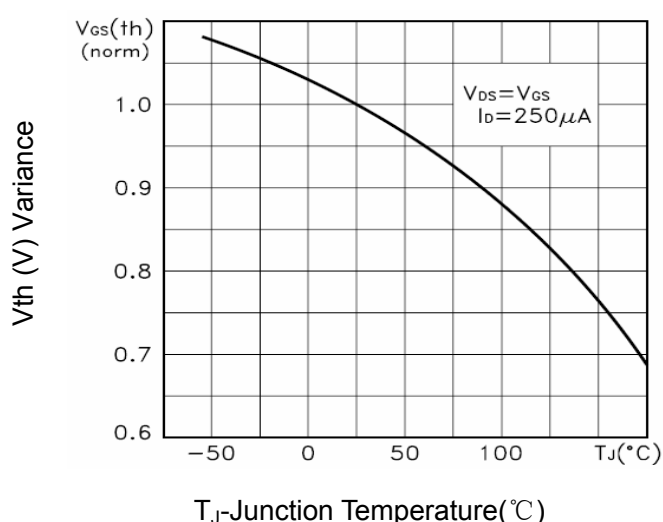


Figure 10 V_{GS(th)} vs Junction Temperature

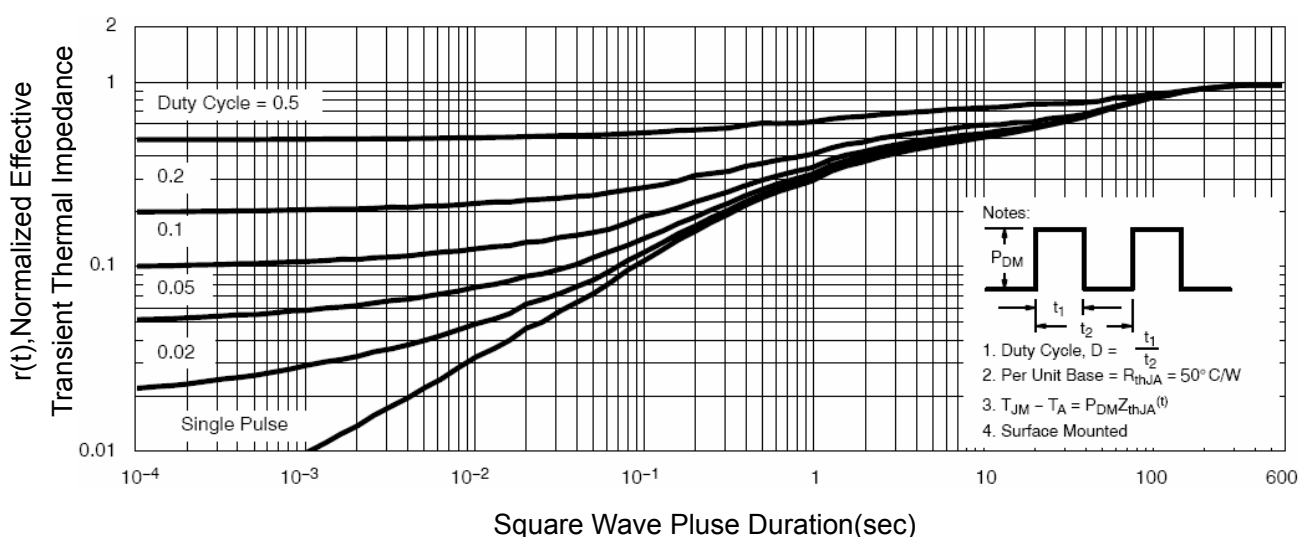
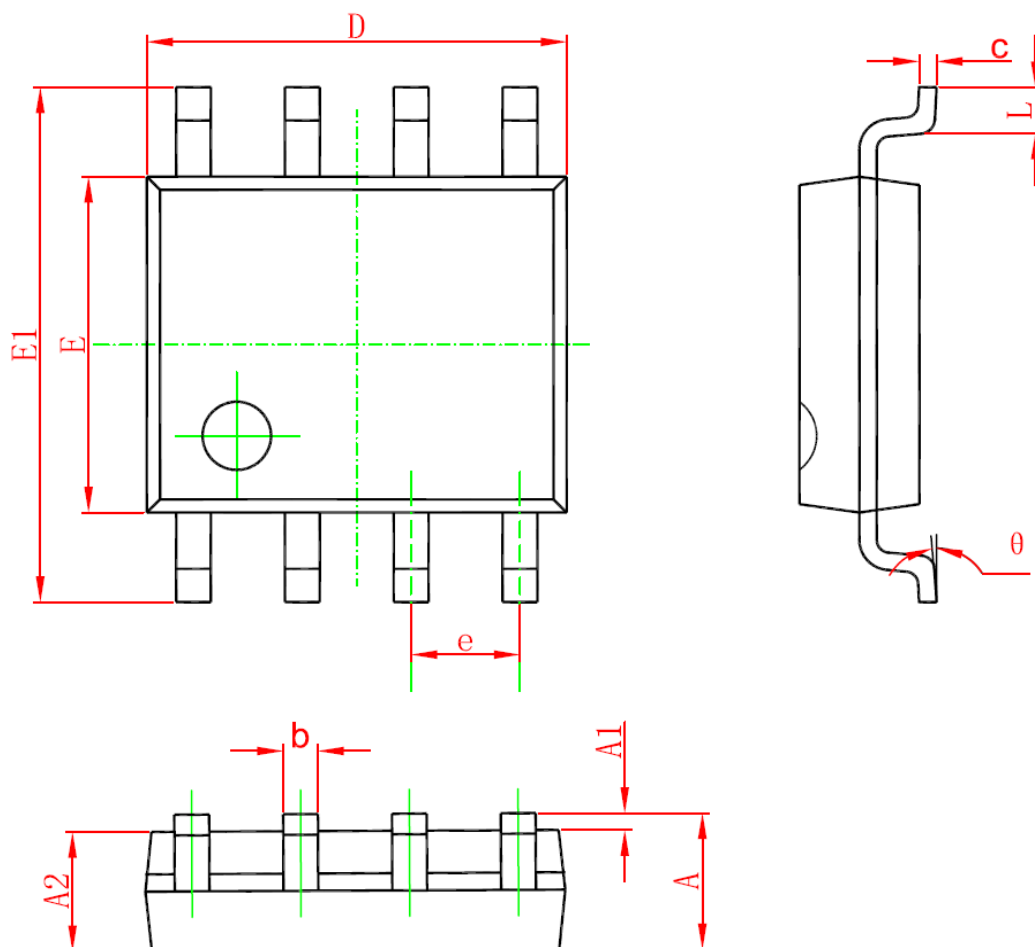


Figure 11 Normalized Maximum Transient Thermal Impedance

SOP-8 PACKAGE IN FORMATION



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270 (BSC)		0.050 (BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°

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